TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

# 2SK2036

High Speed Switching Applications Analog Switching Applications

- High input impedance.
- Low gate threshold voltage: V<sub>th</sub> = 0.5~1.5 V
- Excellent switching times:  $t_{on} = 0.28 \ \mu s \ (typ.)$

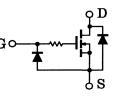
toff = 0.34 μs (typ.)

- Small package
- Enhancement-mode

#### Marking

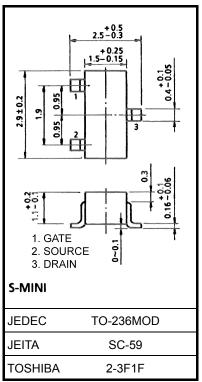
#### **Equivalent Circuit**





## Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V <sub>DS</sub>	20	V
Gate-source voltage	V <sub>GSS</sub>	10	V
Drain current	۱ <sub>D</sub>	100	mA
Drain power dissipation	PD	200	mW
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature range	T <sub>stg</sub>	-55~150	°C



Weight: 0.012 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

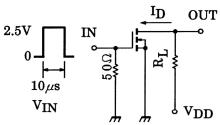
Note: This transistor is electrostatic sensitive device. Please handle with caution.

Unit: mm

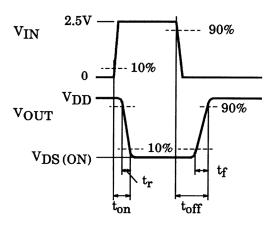
**Electrical Characteristics (Ta = 25°C)** 

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{GS} = 10 \text{ V}, \text{ V}_{DS} = 0$	_		1	μA
Drain-source breakdown voltage		V (BR) DSS	$I_D = 100 \ \mu A, \ V_{GS} = 0$	20	_	_	V
Drain cut-off curre	nt	I <sub>DSS</sub>	$V_{DS} = 20 \text{ V}, \text{ V}_{GS} = 0$	_	_	1	μA
Gate threshold vo	Itage	V <sub>th</sub>	$V_{DS} = 3 \text{ V}, \text{ I}_{D} = 0.1 \text{ mA}$	0.5	_	1.5	V
Forward transfer a	admittance	Y <sub>fs</sub>	$V_{DS} = 3 \text{ V}, \text{ I}_{D} = 10 \text{ mA}$	35	62	_	mS
Drain-source ON r	resistance	R <sub>DS (ON)</sub>	$I_D = 10 \text{ mA}, V_{GS} = 2.5 \text{ V}$	_	3.5	6	Ω
Input capacitance		C <sub>iss</sub>	$V_{DS} = 3 \text{ V}, \text{ V}_{GS} = 0, \text{ f} = 1 \text{ MHz}$	_	14	_	pF
Reverse transfer capacitance		C <sub>rss</sub>	$V_{DS} = 3 \text{ V}, \text{ V}_{GS} = 0, \text{ f} = 1 \text{ MHz}$	_	5.3	_	pF
Output capacitance		C <sub>oss</sub>	$V_{DS} = 3 \text{ V}, \text{ V}_{GS} = 0, \text{ f} = 1 \text{ MHz}$	_	16	_	pF
Switching time	Turn-on time	t <sub>on</sub>	$V_{DD} = 3 \text{ V}, \text{ I}_{D} = 10 \text{ mA}, \text{ V}_{GS} = 0 \text{~} 2.5 \text{ V}$	_	0.28	_	μs
	Turn-off time	t <sub>off</sub>	$V_{DD}$ = 3 V, $I_D$ = 10 mA, $V_{GS}$ = 0~2.5 V	_	0.34	_	

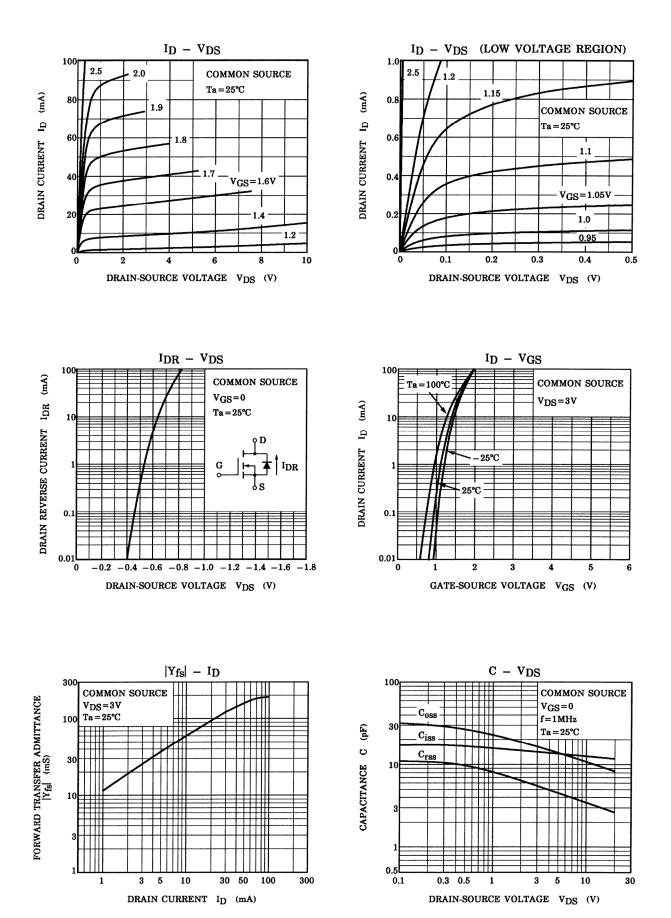
## Switching Time Test Circuit



 $V_{DD}=3V$ D. U.  $\leq 1\%$ V<sub>IN</sub> : t<sub>r</sub>, t<sub>f</sub><5ns (Z<sub>out</sub>=50 $\Omega$ ) COMMON SOURCE Ta=25°C

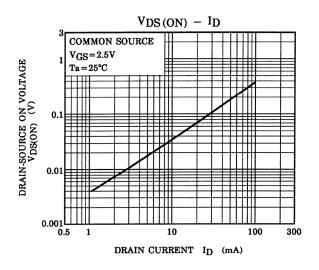


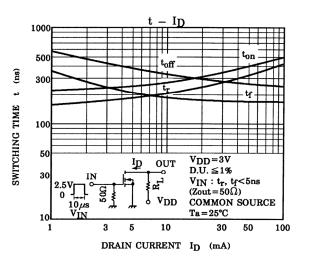
# TOSHIBA

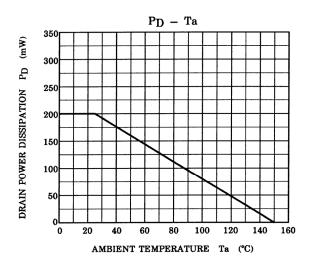


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# **TOSHIBA**







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20070701-EN GENERAL

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